

200 Volt, 1.5Ω HEXFET

HEXFET technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry achieves very low on-state resistance combined with high transconductance.

HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and electrical parameter temperature stability. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits, and virtually any application where high reliability is required.

Product Summary

Part Number	BV _{DSS}	R _{Ds(on)}	I _D
JANTX2N6784	200V	1.5Ω	2.25A
JANTXV2N6784			

Features:

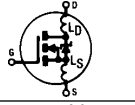
- Avalanche Energy Rating
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed

Absolute Maximum Ratings

	Parameter	JANTX2N6784, JANTXV2N6784	Units
I _D @ V _{GS} = 10V, T _C = 25°C	Continuous Drain Current	2.25	A
I _D @ V _{GS} = 10V, T _C = 100°C	Continuous Drain Current	1.50	
I _{DM}	Pulsed Drain Current ①	9.0	
P _D @ T _C = 25°C	Max. Power Dissipation	15	W
	Linear Derating Factor	0.12	W/K ⑤
V _{GS}	Gate-to-Source Voltage	±20	V
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10.5 seconds)	
	Weight	0.98 (typical)	

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Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	V _{GS} = 0V, I _D = 1.0 mA
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.25	—	V/°C	Reference to 25°C, I _D = 1.0 mA
RDS(on)	Static Drain-to-Source	—	—	1.5	Ω	V _{GS} = 10V, I _D = 1.5A ④
	On-State Resistance	—	—	1.725		
VGS(th)	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	0.9	—	—	S (r)	V _{DS} > 15V, I _{DS} = 1.5A ④
IDSS	Zero Gate Voltage Drain Current	—	—	25	μA	V _{DS} = 0.8 x Max Rating, V _{GS} = 0V
		—	—	250		
IGSS	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
IGSS	Gate-to-Source Leakage Reverse	—	—	-100	nA	V _{GS} = -20V
Q _g	Total Gate Charge	4.3	—	6.2	nC	V _{GS} = 10V, I _D = 2.25A V _{DS} = Max. Rating x 0.5 see figures 6 and 13
Q _{gs}	Gate-to-Source Charge	0.7	—	1.2		
Q _{gd}	Gate-to-Drain ("Miller") Charge	0.5	—	5.0		
t _{d(on)}	Turn-On Delay Time	—	—	15	ns	V _{DD} = 100V, I _D = 2.25A, R _G = 7.5Ω, V _{GS} = 10V see figure 10
t _r	Rise Time	—	—	20		
t _{d(off)}	Turn-Off Delay Time	—	—	30		
t _f	Fall Time	—	—	20		
LD	Internal Drain Inductance	—	5.0	—	nH	<p>Measured from the drain lead, 6mm (0.25 in.) from package to center of die.</p> <p>Modified MOSFET symbol showing the internal inductances.</p> 
LS	Internal Source Inductance	—	15	—		
C _{iss}	Input Capacitance	—	140	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0 MHz see figure 5
C _{oss}	Output Capacitance	—	55	—		
C _{rss}	Reverse Transfer Capacitance	—	8.6	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	2.25	A	Modified MOSFET symbol showing the integral reverse p-n junction rectifier.
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	9.0		
V _{SD}	Diode Forward Voltage	—	—	1.5	V	T _j = 25°C, I _S = 2.25A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	350	ns	T _j = 25°C, I _F = 2.25A, di/dt ≤ 100A/μs V _{DD} ≤ 50V ④
Q _{RR}	Reverse Recovery Charge	—	—	3.0	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	8.3	K/W	Typical socket mount
R _{thJA}	Junction-to-Ambient	—	—	175		

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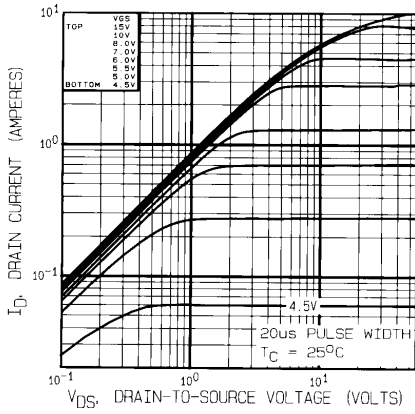


Fig. 1 — Typical Output Characteristics
 $T_C = 25^\circ\text{C}$

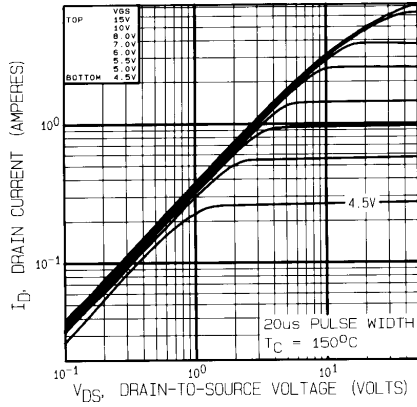


Fig. 2 — Typical Output Characteristics
 $T_C = 150^\circ\text{C}$

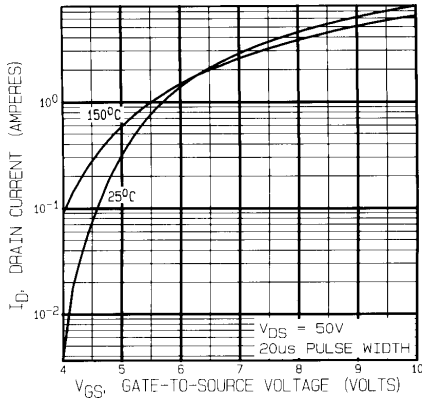


Fig. 3 — Typical Transfer Characteristics

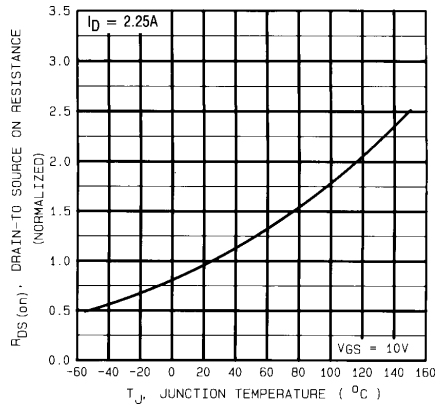


Fig. 4 — Normalized On-Resistance Vs. Temperature

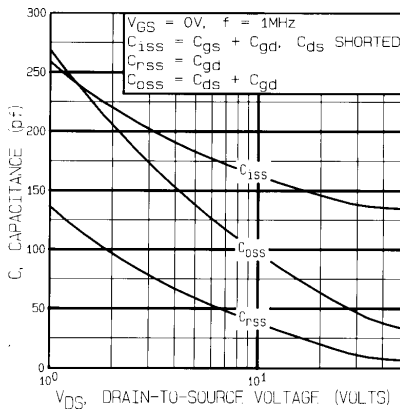


Fig. 5 — Typical Capacitance Vs. Drain-to-Source Voltage

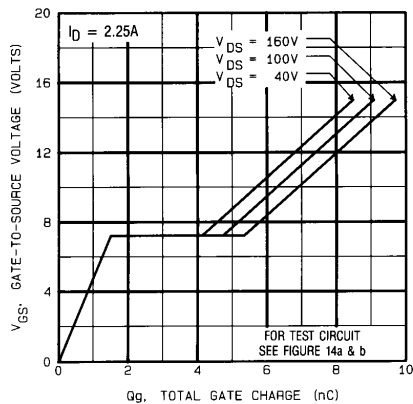


Fig. 6 — Typical Gate Charge Vs. Gate-to-Source Voltage

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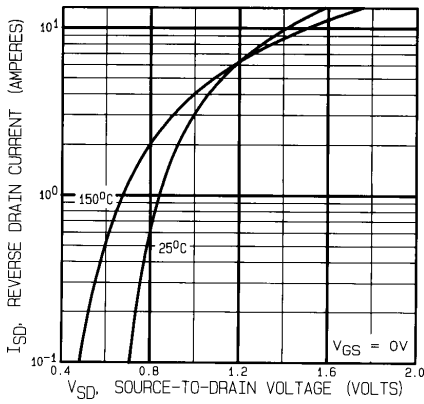


Fig. 7 — Typical Source-to-Drain Diode Forward Voltage

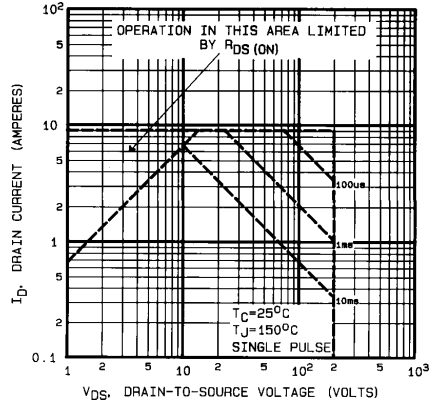


Fig. 8 — Maximum Safe Operating Area

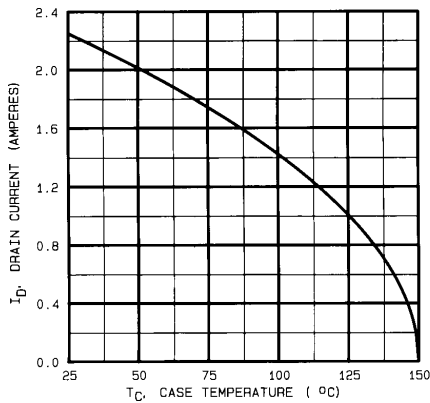


Fig. 9 — Maximum Drain Current Vs. Case Temperature

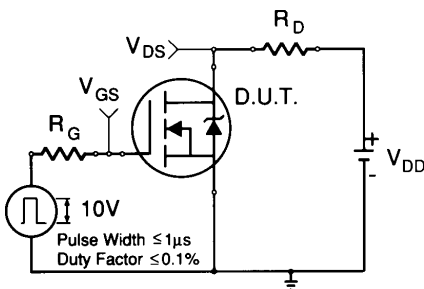


Fig. 10a — Switching Time Test Circuit

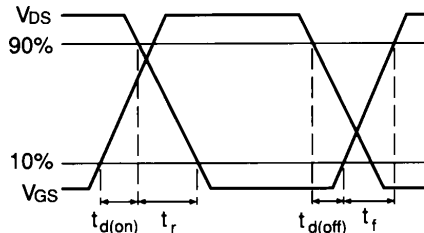


Fig. 10b — Switching Time Waveforms

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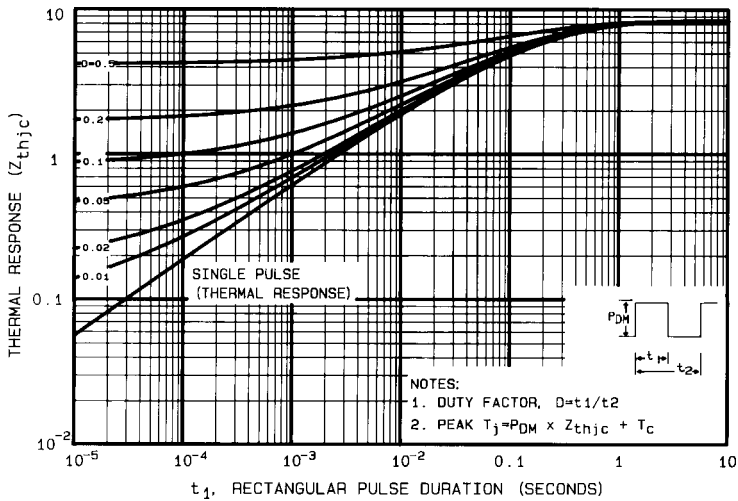


Fig. 11 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

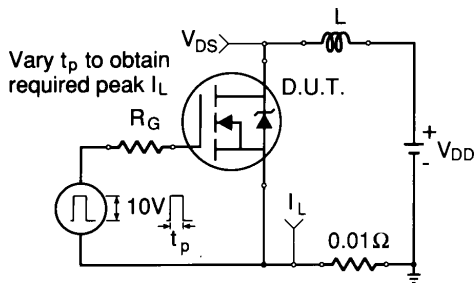


Fig. 12a — Unclamped Inductive Test Circuit

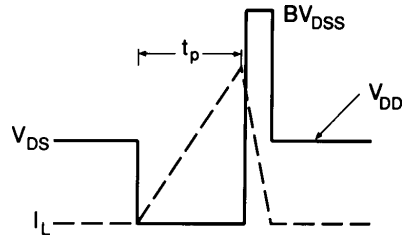


Fig. 12b — Unclamped Inductive Waveforms

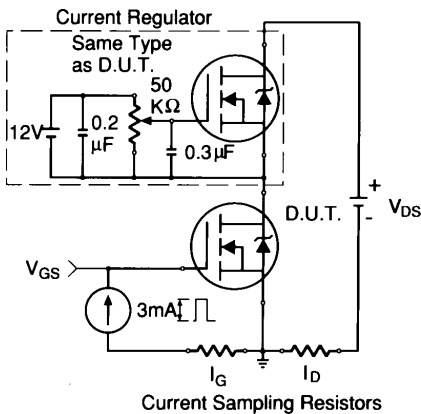


Fig. 13a — Gate Charge Test Circuit

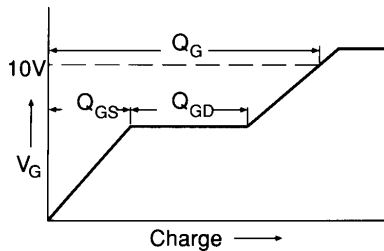
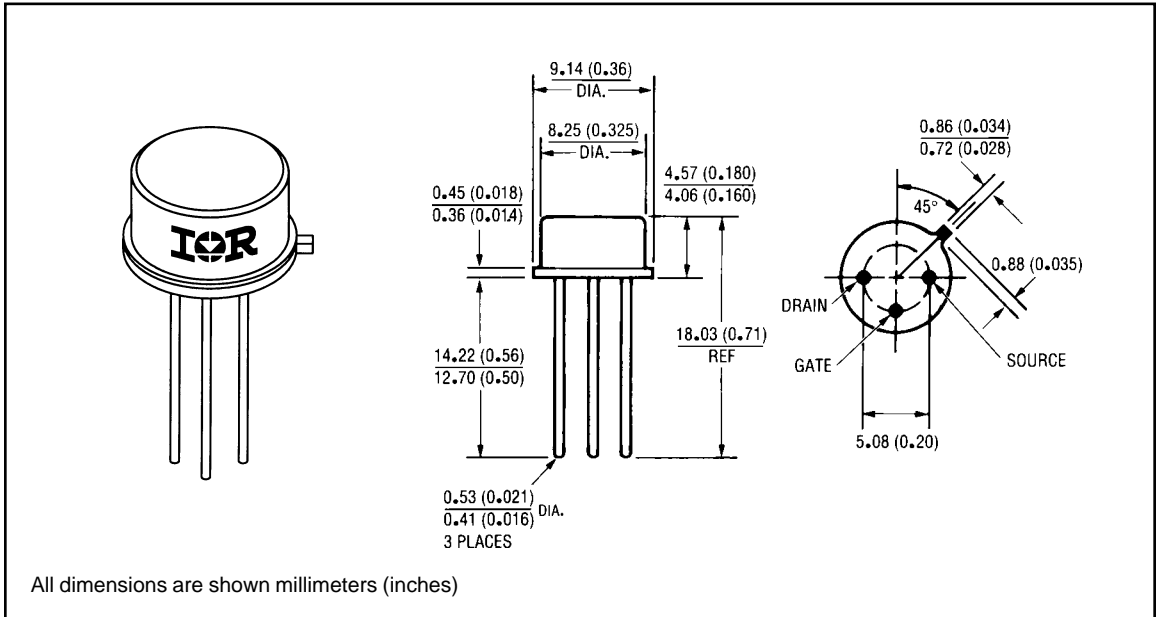


Fig. 13b — Basic Gate Charge Waveform

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- ① Repetitive Rating; Pulse width limited by maximum junction temperature. (see figure 11)
- ② @ $V_{DD} = 50V$, Starting $T_J = 25^\circ C$,
 $E_{AS} = [0.5 * L * (I_L^2) * [BV_{DSS}/(BV_{DSS}-V_{DD})]]$
 Peak $I_L = 2.25A$, $V_{GS} = 10V$, $25 \leq R_G \leq 200\Omega$
- ③ $I_{SD} \leq 2.25A$, $di/dt \leq 70A/\mu s$,
 $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ $K/W = ^\circ C/W$
 $W/K = W/^\circ C$

Case Outline and Dimensions — TO-205AF (Modified TO-39)



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